ELSEVIER

Journal of Crystal Growth 164 (1995) 496–501

JOURNAL OF CRYSTAL GROWTH

Author index

Abernathy, C.R., see Mackenzie 164 (1996) 143
Abernathy, C.R., see Santana 164 (1996) 248
Abernathy, C.R., see Antonell 164 (1996) 420
Ailey, S.K., see Davi 164 (1996) 132
Albrecht, P., see Kb 164 (1996) 449
Alexandre, F., see 164 (1996) 314
Algra, E., see W 164 (1996) 223
Alkemade, P., see Werner 164 (1996) 223
Allen, S.J., see Sadw 164 (1996) 285
Allovon, M., see Lega 164 (1996) 314
Amano, C., A. Rudra, P. C , J.F. Carlin and M. Ilegems, Growth temperature dependence of the interfacet migration in chemical beam epitaxy of InP on non-planar substrates 164 (1996) 321
Ancilotti, M., see Benchimol 164 (1996) 22
Ando, H., S. Yamaura and T. Fujii, Recent progress in the multi-wafer CBE system 164 (1996) 1
Antonell, M.J., C.R. Abernathy and R.W. Gedridge, Tellurium doping of InP using triisopropylindium–diisopropyltellurium (TIPIn–DIPTe) 164 (1996) 420
Aoyagi, Y., see Zhang 164 (1996) 28
Araki, T., see Inoue 164 (1996) 88
Asahi, H., see Yamamoto 164 (1996) 117
Asami, K., see Yamamoto 164 (1996) 117
Aspnes, D.E., see Dietz 164 (1996) 34

Bachem, K.H., see Davidson 164 (1996) 396
Bachmann, K.J., see Dietz 164 (1996) 34
Baumeister, H., see Veuhoff 164 (1996) 402
Beam III, E.A. and H.F. Chau, The use of CBr_4 and $SiBr_4$ doping in MOMBE and application to InP-based heterojunction bipolar transistor structures 164 (1996) 389
Beanland, R., see Boyd 164 (1996) 51
Benchimol, J.L. and M. Ancilotti, Simple high conductance gas line for high growth rate and low transient 164 (1996) 22
Benchimol, J.L., see Lamare 164 (1996) 122
Benchimol, J.L., see Legay 164 (1996) 314
Bensaoula, A., see Taferner 164 (1996) 167
Bensaoula, A., W.T. Taferner, E. Kim and A. Bousetta, The nitridation of GaAs and GaN deposition on GaAs examined by in situ time-of-flight low energy ion scattering and RHEED 164 (1996) 185
Bensaoula, A. and A. Freundlich, Strain balanced GaP/GaAs/InP/GaAs superlattices: structural and electronic properties 164 (1996) 271
Bensaoula, A., see Vilela 164 (1996) 465
Bi, W.G., X.B. Mei and C.W. Tu, Growth studies of GaP on Si by gas-source molecular beam epitaxy 164 (1996) 256
Bidnyk, S., see Wong 164 (1996) 159
Böttcher, J., see Schelhase 164 (1996) 339
Bousetta, A., see Taferner 164 (1996) 167
Bousetta, A., see Bensaoula 164 (1996) 185
Boyd, A.R., T.B. Joyce and R. Beanland, An in-situ laser-light scattering study of the development of surface topography during GaAs and $In_xGa_{1-x}As$ chemical beam epitaxy 164 (1996) 51
Boyd, A.R., T.J. Bullough, T. Farrell and T.B. Joyce, Growth mechanisms and morphology of Ar^+ laser assisted CBE of GaAs 164 (1996) 71
Brehmer, D., see Sadwick 164 (1996) 285
Bullough, T.J., see Boyd 164 (1996) 71
Bullough, T.J., see Davidson 164 (1996) 383
Butzke, S., see Werner 164 (1996) 223

Cacciatore, C., see Rigo 164 (1996) 430
Carlin, J.F., see Amano 164 (1996) 321
Carlin, J.F., A. Rudra and M. Ilegems, Pseudomorphic InGaAs/In(Ga)P bidimensional electron gas grown by chemical beam epitaxy 164 (1996) 470
Carpenter, G., see Van Hove 164 (1996) 154
Chandrasekhar, S., see Hamm 164 (1996) 362
Chang, Y.G., see Chen 164 (1996) 460
Chau, H.F., see Beam III 164 (1996) 389
Chen, J.X., see Li 164 (1996) 84
Chen, J.X., A.Z. Li, Y.C. Ren, M. Qi and Y.G. Chang, Parametric study on lattice-matched and pseudomorphic InGaAs/InAlAs/InP modulation-doped heterostructures grown by GSMBE 164 (1996) 460
Chen, W.L., G.O. Munns, X. Wang and G.I. Haddad, Co-integration of high speed InP-

ELSEVIER

Journal of Crystal Growth 164 (1995) 496–501

JOURNAL OF CRYSTAL GROWTH

Author index

Abernathy, C.R., see Mackenzie 164 (1996) 143
Abernathy, C.R., see Santana 164 (1996) 248
Abernathy, C.R., see Antonell 164 (1996) 420
Ailey, S.K., see Davi 164 (1996) 132
Albrecht, P., see Kb 164 (1996) 449
Alexandre, F., see 164 (1996) 314
Algra, E., see W 164 (1996) 223
Alkemade, P., see Werner 164 (1996) 223
Allen, S.J., see Sadw 164 (1996) 285
Allovon, M., see Lega 164 (1996) 314
Amano, C., A. Rudra, P. C , J.F. Carlin and M. Ilegems, Growth temperature dependence of the interfacet migration in chemical beam epitaxy of InP on non-planar substrates 164 (1996) 321
Ancilotti, M., see Benchimol 164 (1996) 22
Ando, H., S. Yamaura and T. Fujii, Recent progress in the multi-wafer CBE system 164 (1996) 1
Antonell, M.J., C.R. Abernathy and R.W. Gedridge, Tellurium doping of InP using triisopropylindium–diisopropyltellurium (TIPIn–DIPTe) 164 (1996) 420
Aoyagi, Y., see Zhang 164 (1996) 28
Araki, T., see Inoue 164 (1996) 88
Asahi, H., see Yamamoto 164 (1996) 117
Asami, K., see Yamamoto 164 (1996) 117
Aspnes, D.E., see Dietz 164 (1996) 34

Bachem, K.H., see Davidson 164 (1996) 396
Bachmann, K.J., see Dietz 164 (1996) 34
Baumeister, H., see Veuhoff 164 (1996) 402
Beam III, E.A. and H.F. Chau, The use of CBr_4 and $SiBr_4$ doping in MOMBE and application to InP-based heterojunction bipolar transistor structures 164 (1996) 389
Beanland, R., see Boyd 164 (1996) 51
Benchimol, J.L. and M. Ancilotti, Simple high conductance gas line for high growth rate and low transient 164 (1996) 22
Benchimol, J.L., see Lamare 164 (1996) 122
Benchimol, J.L., see Legay 164 (1996) 314
Bensaoula, A., see Taferner 164 (1996) 167
Bensaoula, A., W.T. Taferner, E. Kim and A. Bousetta, The nitridation of GaAs and GaN deposition on GaAs examined by in situ time-of-flight low energy ion scattering and RHEED 164 (1996) 185
Bensaoula, A. and A. Freundlich, Strain balanced GaP/GaAs/InP/GaAs superlattices: structural and electronic properties 164 (1996) 271
Bensaoula, A., see Vilela 164 (1996) 465
Bi, W.G., X.B. Mei and C.W. Tu, Growth studies of GaP on Si by gas-source molecular beam epitaxy 164 (1996) 256
Bidnyk, S., see Wong 164 (1996) 159
Böttcher, J., see Schelhase 164 (1996) 339
Bousetta, A., see Taferner 164 (1996) 167
Bousetta, A., see Bensaoula 164 (1996) 185
Boyd, A.R., T.B. Joyce and R. Beanland, An in-situ laser-light scattering study of the development of surface topography during GaAs and $In_xGa_{1-x}As$ chemical beam epitaxy 164 (1996) 51
Boyd, A.R., T.J. Bullough, T. Farrell and T.B. Joyce, Growth mechanisms and morphology of Ar^+ laser assisted CBE of GaAs 164 (1996) 71
Brehmer, D., see Sadwick 164 (1996) 285
Bullough, T.J., see Boyd 164 (1996) 71
Bullough, T.J., see Davidson 164 (1996) 383
Butzke, S., see Werner 164 (1996) 223

Cacciatore, C., see Rigo 164 (1996) 430
Carlin, J.F., see Amano 164 (1996) 321
Carlin, J.F., A. Rudra and M. Ilegems, Pseudomorphic InGaAs/In(Ga)P bidimensional electron gas grown by chemical beam epitaxy 164 (1996) 470
Carpenter, G., see Van Hove 164 (1996) 154
Chandrasekhar, S., see Hamm 164 (1996) 362
Chang, Y.G., see Chen 164 (1996) 460
Chau, H.F., see Beam III 164 (1996) 389
Chen, J.X., see Li 164 (1996) 84
Chen, J.X., A.Z. Li, Y.C. Ren, M. Qi and Y.G. Chang, Parametric study on lattice-matched and pseudomorphic InGaAs/InAlAs/InP modulation-doped heterostructures grown by GSMBE 164 (1996) 460
Chen, W.L., G.O. Munns, X. Wang and G.I. Haddad, Co-integration of high speed InP-

based HBTs and RTDs using chemical beam epitaxy 164 (1996) 454
Chen, W.L., see Munns 164 (1996) 476
Chow, P.P., see Van Hove 164 (1996) 154
Cordier, Y., see Ortion 164 (1996) 97
Cotta, M.A., M.M.G. de Carvalho, M.A.A. Pudenzi, K.M.I. Landers, C.F. de Souza, R.B. Martins, R. Landers and O. Teschke, Surface morphologies of Be-doped homoepitaxial InP films 164 (1996) 409
Cui, J., see Zhang 164 (1996) 28

Davidson, B.R., L. Hart, R.C. Newman, T.B. Joyce and T.J. Bullough, Characterization of carbon delta-doping GaAs superlattices grown by chemical beam epitaxy using CBr_4 164 (1996) 383
Davidson, B.R., R.C. Newman, T. Kanedo, O. Naji and K.H. Bachem, The rotation of the alignment by 90° of $(H–(C_{As})_2)$ complexes resulting from metalorganic molecular beam epitaxy or metalorganic vapour phase epitaxy growth on GaAs(001) using trimethylgallium 164 (1996) 396
Davies, G.J., see Foord 164 (1996) 190
Davies, G.J., see Foord 164 (1996) 208
Davis, R.F., S. Tanaka, L.B. Rowland, R.S. Kern, Z. Sitar, S.K. Ailey and C. Wang, Growth of SiC and III–V nitride thin films via gas-source molecular beam epitaxy and their characterization 164 (1996) 132
De Carvalho, M.M.G., see Cotta 164 (1996) 409
De Franceschi, R., see Rigo 164 (1996) 327
De Lange, B., see Werner 164 (1996) 223
De Souza, C.F., see Cotta 164 (1996) 409
Deng, F., see Wong 164 (1996) 159
Dietz, N., U. Rossow, D.E. Aspnes and K.J. Bachmann, Real-time optical monitoring of $Ga_xIn_{1-x}P$ and GaP heteroepitaxy on Si under pulsed chemical beam conditions 164 (1996) 34
Dong, H.K., see Li 164 (1996) 112
Dong, H.K., see Wong 164 (1996) 159
Dong, H.K., see Li 164 (1996) 180
Dorren, B.H.P., see Vreeburg 164 (1996) 442

Farrell, T., see Boyd 164 (1996) 71
Fernández, J.M., see Zhang 164 (1996) 40
Fernández, J.M., see Joyce 164 (1996) 214
Fernández, J.M., L. Hart, X.M. Zhang, M.H. Xie, J. Zhang and B.A. Joyce, Silicon/silicon–germanium multiple quantum wells grown by gas-source molecular beam epitaxy: hydrogen coverage and interfacial abruptness 164 (1996) 241
Foord, J.S., C.L. Levoguer and G.J. Davies, An investigation of ZnSe growth by chemical beam epitaxy using modulated beam scattering and related techniques 164 (1996) 190
Foord, J.S., K.P. Loh, N.K. Singh, R.B. Jackman and G.J. Davies, Growth and mechanistic studies of diamond formation by chemical beam epitaxy using methyl and acetylene precursors 164 (1996) 208
Fouchet, S., see Legay 164 (1996) 314
Freer, R.W., see Whitaker 164 (1996) 296
Freundlich, A., see Bensaoula 164 (1996) 271
Freundlich, A., see Vilela 164 (1996) 465
Fujii, T., see Ando 164 (1996) 1
Fujita, Sg., see Fujita 164 (1996) 196
Fujita, Sz., Y. Kawakami and Sg. Fujita, MO(GS)MBE and photo-MO(GS)MBE of II–VI semiconductors 164 (1996) 196
Fukuchi, F., see Oh 164 (1996) 425

Garcia, J.Ch., see Ortion 164 (1996) 97
Gasparotto, A., see Rigo 164 (1996) 430
Gedridge, R.W., see Sadwick 164 (1996) 285
Gedridge, R.W., see Antonell 164 (1996) 420
Geva, M., see Hamm 164 (1996) 362
Gibis, R., see Schelhase 164 (1996) 339
Gibis, R., see Künzel 164 (1996) 449
Gonda, S., see Yamamoto 164 (1996) 117
Goodhew, P.J., see Joyce 164 (1996) 371
Goodhew, P.J., see Petkos 164 (1996) 415
Goronkin, H., see Shiralagi 164 (1996) 334
Gotoda, M., H. Sugimoto, T. Isu and M. Nunoshita, Grown mirrors of InP formed by dry etching and selective CBE regrowth for short cavity lasers 164 (1996) 308
Grant, J.T., see Li 164 (1996) 180
Grattepain, C., see Ortion 164 (1996) 97
Grunberg, P., see Amano 164 (1996) 321

Haddad, G.I., see Chen 164 (1996) 454
Haddad, G.I., see Munns 164 (1996) 476
Hamacher, M., see Künzel 164 (1996) 449
Hamm, R.A., S. Chandrasekhar, L. Lunardi, M. Geva, R. Malik, D. Humphrey and R. Ryan, Materials and electrical characteristics of carbon-doped $Ga_{0.47}In_{0.53}As$ using carbon-tetrabromide by MOMBE for HBT device applications 164 (1996) 362
Hart, L., see Fernández 164 (1996) 241
Hart, L., see Davidson 164 (1996) 383
Hayashi, T., see Yamamoto 164 (1996) 117
Hays, J., see Wong 164 (1996) 159
Heinecke, H., see Marheineke 164 (1996) 16
Heinecke, H., see Wachter 164 (1996) 302
Heinecke, H., see Veuhoff 164 (1996) 402
Homma, Y., see Inoue 164 (1996) 88
Hou Xun, see Wang Xiaoliang 164 (1996) 281
Humphrey, D., see Hamm 164 (1996) 362
Hwu, R.J., see Sadwick 164 (1996) 285

Ilegems, M., see Amano 164 (1996) 321
Ilegems, M., see Carlin 164 (1996) 470

Inoue, N., Y. Homma, J. Osaka and T. Araki, Behavior of monolayer holes on MBE grown GaAs surfaces during annealing revealed by in situ scanning electron microscopy 164 (1996) 88
Isu, T., see Gotoda 164 (1996) 308

Jackman, R.B., see Foord 164 (1996) 208
Jeppesen, S., see Junno 164 (1996) 66
Jeppesen, S., see Miller 164 (1996) 345
Johnson, A.D., see Whitaker 164 (1996) 125
Jones, K.S., see Santana 164 (1996) 248
Jones, T.S., see Naji 164 (1996) 58
Joyce, B.A., see Zhang 164 (1996) 40
Joyce, B.A., see Naji 164 (1996) 58
Joyce, B.A., J.M. Fernández, M.H. Xie, A. Matsumura, J. Zhang and A.G. Taylor, Growth and doping of Si and SiGe films by hydride gas-source molecular beam epitaxy 164 (1996) 214
Joyce, B.A., see Fernández 164 (1996) 241
Joyce, T.B., see Boyd 164 (1996) 51
Joyce, T.B., see Boyd 164 (1996) 71
Joyce, T.B., S.P. Westwater, P.J. Goodhew and R.E. Pritchard, Growth of carbon-doped GaAs, AlGaAs and InGaAs by chemical beam epitaxy and the application of in-situ monitoring 164 (1996) 371
Joyce, T.B., see Davidson 164 (1996) 383
Joyce, T.B., see Petkos 164 (1996) 415
Junno, B., S. Jeppesen, M.S. Miller and L. Samuelson, A comparison of RHEED reconstruction phases on (100) InAs, GaAs and InP 164 (1996) 66

Kanedo, T., see Davidson 164 (1996) 396
Kaneko, T., see Naji 164 (1996) 58
Kang, H.-C., see Oh 164 (1996) 425
Kawakami, Y., see Fujita 164 (1996) 196
Kern, R.S., see Davis 164 (1996) 132
Kim, C.W., G.B. Stringfellow and L.P. Sadwick, CBE growth of InP using BPE and TBP: a comparative study 164 (1996) 104
Kim, E., see Taferner 164 (1996) 167
Kim, E., see Bensaoula 164 (1996) 185
Kim, Sung-Bock, Seong-Ju Park, Jeong-Rae Ro and El-Hang Lee, Fabrication of InGaAs/GaAs quantum wires on a non-(111) V-grooved GaAs substrate by chemical beam epitaxy 164 (1996) 356
Kim, Sung-Bock, see Ro 164 (1996) 377
Kitatani, T., see Kondow 164 (1996) 175
Konagai, M., see Oh 164 (1996) 425
Kondow, M., K. Uomi, T. Kitatani, S. Watahiki and Y. Yazawa, Extremely large N content (up to 10%) in GaNAs grown by gas-source molecular beam epitaxy 164 (1996) 175
Kong Meiying, see Wang Xiaoliang 164 (1996) 281
Kowalski, B., see Miller 164 (1996) 345
Künzel, H., see Schelhase 164 (1996) 339
Künzel, H., P. Albrecht, R. Gibis, M. Hamacher and S. Schelhase, MOMBE growth of high quality GaInAsP ($\lambda_g = 1.05\ \mu m$) for waveguide applications 164 (1996) 449
Kuo, H.C., see Sato 164 (1996) 47
Kuo, J.M., see Sato 164 (1996) 47

Lamare, B., J.L. Benchimol, P. Ossart and G. Le Roux, CBE growth of InGaAs(P) alloys using TDMAAs and TBP 164 (1996) 122
Landers, K.M.I., see Cotta 164 (1996) 409
Landers, R., see Cotta 164 (1996) 409
Lau, S.S., see Wong 164 (1996) 159
Laune, F., see Legay 164 (1996) 314
Le Roux, G., see Lamare 164 (1996) 122
Lee, El-Hang, see Kim 164 (1996) 356
Lee, El-Hang, see Ro 164 (1996) 377
Lee, H.P., see Sato 164 (1996) 47
Lee, P.P., see Sadwick 164 (1996) 285
Lees, A.K., see Zhang 164 (1996) 40
Legay, P., F. Alexandre, J.L. Benchimol, M. Allovon, F. Laune and S. Fouchet, Selective area chemical beam epitaxy for butt-coupling integration 164 (1996) 314
Levoguer, C.L., see Foord 164 (1996) 190
Lew, A.Y., see Yan 164 (1996) 77
Leys, M.R., see Rongen 164 (1996) 263
Leys, M.R., see Vreeburg 164 (1996) 442
Li, A.Z., J.X. Chen, M. Qi and Y.C. Ren, The effect of III–V ratio at the substrate surface on the quality of inP grown by GSMBE 164 (1996) 84
Li, A.Z., see Chen 164 (1996) 460
Li, N.Y., H.K. Dong, W.S. Wong and C.W. Tu, An evaluation of alternative precursors in chemical beam epitaxy: tris-dimethylamino-arsenic, tris-dimethylaminophosphorus, and tertiarybutylphosphine 164 (1996) 112
Li, N.Y., see Wong 164 (1996) 159
Li, N.Y., W.S. Wong, D.H. Tomich, H.K. Dong, J.S. Solomon, J.T. Grant and C.W. Tu, Growth study of chemical beam epitaxy of GaN_xP_{1-x} using NH_3 and tertiarybutylphosphine 164 (1996) 180
Li, S., Q. Xiang, D. Wang and K.L. Wang, Investigation of facet formation and competition in MBE growth 164 (1996) 235
Loh, K.P., see Foord 164 (1996) 208
Lunardi, L., see Hamm 164 (1996) 362

Mackenzie, J.D., C.R. Abernathy, J.D. Stewart and G.T. Muhr, Growth of Group III nitrides by chemical beam epitaxy 164 (1996) 143
Madella, M., see Rigo 164 (1996) 430
Maes, J.W., see Werner 164 (1996) 223
Malik, R., see Hamm 164 (1996) 362
Mandeville, P., see Moore 164 (1996) 485

Marheineke, B., M. Popp and H. Heinecke, Growth of GaInAs(P) using a multiwafer MOMBE 164 (1996) 16
Martin, T., see Whitaker 164 (1996) 125
Martin, T., see Whitaker 164 (1996) 296
Martins, R.B., see Cotta 164 (1996) 409
Matsumura, A., see Joyce 164 (1996) 214
Maximov, I., see Miller 164 (1996) 345
McCormick, K., see Sadwick 164 (1996) 285
Medelci, N., see Vilela 164 (1996) 465
Mei, X.B., see Bi 164 (1996) 256
Miller, M.S., see Junno 164 (1996) 66
Miller, M.S., S. Jeppesen, B. Kowalski, I. Maximov and L. Samuelson, Directional dependence of InAs island formation on patterned GaAs 164 (1996) 345
Miner, C.J., see Moore 164 (1996) 485
Moore, W.T., P. Mandeville, R.W. Streater and C.J. Miner, Device quality AlGaAs grown by chemical beam epitaxy 164 (1996) 485
Muhr, G.T., see Mackenzie 164 (1996) 143
Munns, G.O., see Chen 164 (1996) 454
Munns, G.O., W.L. Chen and G.I. Haddad, Heterojunction bipolar transistors with low temperature Be-doped base grown by CBE 164 (1996) 476

Nagatomo, T., see Okumura 164 (1996) 149
Naji, O., J. Zhang, T. Kaneko, T.S. Jones, J.H. Neave and B.A. Joyce, A detailed time of flight study of the cracking pattern trimethylgallium; implications for MOMBE growth 164 (1996) 58
Naji, O., see Davidson 164 (1996) 396
Nasi, L., see Rigo 164 (1996) 430
Neave, J.H., see Naji 164 (1996) 58
Nelson, E., see Van Hove 164 (1996) 154
Newly, J.P., see Whitaker 164 (1996) 125
Newman, R.C., see Davidson 164 (1996) 383
Newman, R.C., see Davidson 164 (1996) 396
Nikols, M., see Sadwick 164 (1996) 285
Nunoshita, M., see Gotoda 164 (1996) 308

Oei, Y.S., see Rongen 164 (1996) 263
Oei, Y.S., see Vreeburg 164 (1996) 442
Ogle, W., see Tong 164 (1996) 202
Oh, J.-H., F. Fukuchi, H.-C. Kang and M. Konagai, Influence of H_2 on electrical and optical properties of carbon-doped InP grown by MOMBE using tertiarybutylphosphine (TBP) 164 (1996) 425
Ohta, K., see Okumura 164 (1996) 149
Okumura, H. and S. Yoshida, Compositional micro-area modification of GaAs surfaces by an electron beam under phosphorus flux 164 (1996) 92
Okumura, H., K. Ohta, T. Nagatomo and S. Yoshida, Observation of MBE-grown cubic-GaN/GaAs and cubic-GaN/3C–SiC interfaces by high resolution transmission electron microscope 164 (1996) 149
Ortion, J.M., Y. Cordier, J.Ch. Garcia and C. Grattepain, Temperature dependence of of GaAs chemical etching using $AsCl_3$ 164 (1996) 97
Osaka, J., see Inoue 164 (1996) 88
Ossart, P., see Lamare 164 (1996) 122

Papuzza, C., see Rigo 164 (1996) 430
Paraskevopoulos, A., see Schelhase 164 (1996) 339
Park, Seong-Ju, see Kim 164 (1996) 356
Park, Seong-Ju, see Ro 164 (1996) 377
Park, W., see Tong 164 (1996) 202
Patel, M., see Sadwick 164 (1996) 285
Pearton, S.J., see Santana 164 (1996) 248
Pemble, M.E., see Zhang 164 (1996) 40
Petkos, G.M., P.J. Goodhew and T.B. Joyce, Sulphur doping of InGaAs using diethylsulphide 164 (1996) 415
Pidduck, A.J., see Whitaker 164 (1996) 125
Popp, M., see Marheineke 164 (1996) 16
Popp, M., see Veuhoff 164 (1996) 402
Pritchard, R.E., see Joyce 164 (1996) 371
Pudenzi, M.A.A., see Cotta 164 (1996) 409

Qi, M., see Li 164 (1996) 84
Qi, M., see Chen 164 (1996) 460

Radelaar, S., see Werner 164 (1996) 223
Raisbeck, D., see Zhang 164 (1996) 40
Ren, Y.C., see Li 164 (1996) 84
Ren, Y.C., see Chen 164 (1996) 460
Renaud, P., see Vilela 164 (1996) 465
Rigo, C., R. Vincenzoni, A. Stano and R. De Franceschi, Chemical beam epitaxy on patterned substrates of InGaAs/InP heterostructures for optoelectronics and nanostructures applications 164 (1996) 327
Rigo, C., M. Madella, C. Papuzza, C. Cacciatore, A. Stano, A. Gasparotto, G. Salviati and L. Nasi, InP:Fe semi-insulating layers by chemical beam epitaxy 164 (1996) 430
Ro, Jeong-Rae, see Kim 164 (1996) 356
Ro, Jeong-Rae, Seong-Ju Park, Sung-Bock Kim and El-Hang Lee, CBE growth of carbon-doped p-type InGaAs using trimethylindium and unprecracked monoethylarsine as carbon auto-doping precursor 164 (1996) 377
Rongen, R.T.H., M.R. Leys, H. Vonk, J.H. Wolter and Y.S. Oei, Substitution of InP layers to InAs for strain compensation in $Ga_xIn_{1-x}As/InP$ superlattices 164 (1996) 263
Rongen, R.T.H., see Vreeburg 164 (1996) 442
Rossow, U., see Dietz 164 (1996) 34
Rowland, L.B., see Davis 164 (1996) 132
Rudra, A., see Amano 164 (1996) 321
Rudra, A., see Carlin 164 (1996) 470
Ryan, R., see Hamm 164 (1996) 362

Sadwick, L.P., see Kim 164 (1996) 104

Sadwick, L.P., P.P. Lee, M. Patel, M. Nikols, R.J. Hwu, J.E. Shield, D.C. Streit, D. Brehmer, K. McCormick, S.J. Allen and R.W. Gedridge, Epitaxial dysprosium phosphide grown by gas-source and solid-source MBE on gallium arsenide substrates 164 (1996) 285

Salviati, G., see Rigo 164 (1996) 430

Samuelson, L., see Junno 164 (1996) 66

Samuelson, L., see Miller 164 (1996) 345

Santana, C.J., C.R. Abernathy, S.J. Pearton and K.S. Jones, Initial growth stages of Al_x-$Ga_{1-x}P$ on epitaxial silicon 164 (1996) 248

Sasaki, M., see Yoshida 164 (1996) 291

Sato, D.L., H.P. Lee, J.M. Kuo and H.C. Kuo, In-situ pyrometric interferometry monitoring of $In_{0.5}Ga_{0.5}P/In_{0.5}Al_{0.5}P$ material systems during gas-source molecular beam epitaxy growth 164 (1996) 47

Schelhase, S., J. Böttcher, R. Gibis, H. Künzel and A. Paraskevopoulos, MOMBE selective infill growth of InP:Si and InGaAs:Si and large area MOMBE regrowth 164 (1996) 339

Schelhase, S., see Künzel 164 (1996) 449

Shen, J., see Tsui 164 (1996) 491

Shield, J.E., see Sadwick 164 (1996) 285

Shiralagi, K., M. Walther, R. Tsui and H. Goronkin, Selective InAs growth by chemical beam epitaxy 164 (1996) 334

Shiralagi, K., see Tsui 164 (1996) 491

Shukla, N., see Zhang 164 (1996) 40

Singh, N.K., see Foord 164 (1996) 208

Sitar, Z., see Davis 164 (1996) 132

Solomon, J.S., see Li 164 (1996) 180

Somers, M., see Werner 164 (1996) 223

Song, J.J., see Wong 164 (1996) 159

Stano, A., see Rigo 164 (1996) 327

Stano, A., see Rigo 164 (1996) 430

Stewart, J.D., see Mackenzie 164 (1996) 143

Storm, A., see Werner 164 (1996) 223

Streater, R.W., see Moore 164 (1996) 485

Streit, D.C., see Sadwick 164 (1996) 285

Stringfellow, G.B., see Kim 164 (1996) 104

Sugimoto, H., see Gotoda 164 (1996) 308

Sugiura, H., MOMBE growth of InAsP laser materials 164 (1996) 434

Summers, C.J., see Tong 164 (1996) 202

Sun Dianzhao, see Wang Xiaoliang 164 (1996) 281

Taferner, W.T., A. Bensaoula, E. Kim and A. Bousetta, The investigation of GaN growth on silicon and sapphire using in-situ time-of-flight low energy ion scattering and RHEED 164 (1996) 167

Taferner, W.T., see Bensaoula 164 (1996) 185

Tanaka, S., see Davis 164 (1996) 132

Taylor, A.G., see Zhang 164 (1996) 40

Taylor, A.G., see Joyce 164 (1996) 214

Teschke, O., see Cotta 164 (1996) 409

Tomich, D.H., see Li 164 (1996) 180

Tong, W., B.K. Wagner, T.K. Tran, W. Ogle, W. Park and C.J. Summers, Kinetics of chemical beam epitaxy for high quality ZnS film growth 164 (1996) 202

Tran, T.K., see Tong 164 (1996) 202

Treichler, R., see Veuhoff 164 (1996) 402

Tsui, R., see Shiralagi 164 (1996) 334

Tsui, R., K. Shiralagi and J. Shen, Growth of resonant interband tunneling diodes using trimethylamine alane 164 (1996) 491

Tu, C.W., see Yan 164 (1996) 77

Tu, C.W., see Li 164 (1996) 112

Tu, C.W., see Wong 164 (1996) 159

Tu, C.W., see Li 164 (1996) 180

Tu, C.W., see Bi 164 (1996) 256

Tu, C.W., see Yan 164 (1996) 276

Uomi, K., see Kondow 164 (1996) 175

Van der Drift, E., see Werner 164 (1996) 223

Van der Tol, J.J.G.M., see Vreeburg 164 (1996) 442

Van Hove, J.M., G. Carpenter, E. Nelson, A. Wowchak and P.P. Chow, III–N light emitting diodes fabricated using RF nitrogen gas source MBE 164 (1996) 154

Van Rooy, M., see Werner 164 (1996) 223

Verbeek, B.H., see Vreeburg 164 (1996) 442

Veuhoff, E., H. Baumeister, R. Treichler, M. Popp and H. Heinecke, Zn doping of InP/GaInAsP device structures in metalorganic molecular beam epitaxy using diethylzinc 164 (1996) 402

Vilela, M.F., N. Medelci, A. Bensaoula, A. Freundlich and P. Renaud, First epitaxial InP tunnel junctions grown by chemical beam epitaxy 164 (1996) 465

Vincenzoni, R., see Rigo 164 (1996) 327

Vonk, H., see Rongen 164 (1996) 263

Vonk, H., see Vreeburg 164 (1996) 442

Vreeburg, C.G.M., Y.S. Oei, B.H. Verbeek, J.J.G.M. van der Tol, R.T.H. Rongen, H. Vonk, M.R. Leys, B.H.P. Dorren and J.H. Wolter, Strained GaInAs/InP MQW layers grown by CBE for optical components 164 (1996) 442

Wachter, M. and H. Heinecke, Beam geometrical effects on planar selective area epitaxy of InP/GaInAs heterostructures 164 (1996) 302

Wagner, B.K., see Tong 164 (1996) 202

Walther, M., see Shiralagi 164 (1996) 334

Wang, C., see Davis 164 (1996) 132

Wang, D., see Li 164 (1996) 235

Wang, K.L., see Li 164 (1996) 235

Wang, X., see Chen 164 (1996) 454

Wang Xiaoliang, Sun Dianzhao, Kong Meiying, Hou Xun and Zeng Yiping, GSMBE

growth and PL investigation of lattice-matched InGaAs/InP quantum wells 164 (1996) 281
Watahiki, S., see Kondow 164 (1996) 175
Werner, K., A. Storm, S. Butzke, J.W. Maes, M. van Rooy, P. Alkemade, E. Algra, M. Somers, B. de Lange, E. van der Drift, T. Zijlstra and S. Radelaar, Gas source MBE growth of Si/SiGe device materials 164 (1996) 223
Westwater, S.P., see Joyce 164 (1996) 371
Whitaker, T.J., T. Martin, A.D. Johnson, A.J. Pidduck and J.P. Newly, Atomic force microscopy studies of substrate cleaning using tris(dimethylamino)arsenic and tris(dimethylamino)antimony and investigations of surface decomposition mechanisms 164 (1996) 125
Whitaker, T.J., T. Martin and R.W. Freer, Increasing the range of growth temperatures available for GaAs selective area growth using triisopropylgallium and arsine 164 (1996) 296
Wolter, J.H., see Rongen 164 (1996) 263
Wolter, J.H., see Vreeburg 164 (1996) 442
Wong, W.S., see Li 164 (1996) 112
Wong, W.S., N.Y. Li, H.K. Dong, F. Deng, S.S. Lau, C.W. Tu, J. Hays, S. Bidnyk and J.J. Song, Growth of GaN by gas-source molecular beam epitaxy by ammonia and by plasma generated nitrogen radicals 164 (1996) 159
Wong, W.S., see Li 164 (1996) 180
Wowchak, A., see Van Hove 164 (1996) 154

Xiang, Q., see Li 164 (1996) 235
Xie, M.H., see Joyce 164 (1996) 214
Xie, M.H., see Fernández 164 (1996) 241

Yamamoto, K., H. Asahi, T. Hayashi, K. Asami and S. Gonda, Metalorganic molecular beam epitaxy growth and etching of GaSb on flat and high-index surfaces uusing trisdimethylaminoantimony 164 (1996) 117
Yamaura, S., see Ando 164 (1996) 1
Yan, C.H., A.Y. Lew, E.T. Yu and C.W. Tu, P_2-induced P/As exchange on GaAs during gas-source molecular beam epitaxy growth interruptions 164 (1996) 77
Yan, C.H. and C.W. Tu, Synthesis of highly strained $In_yGa_{1-y}P/In_xGa_{1-x}As/In_yGa_{1-y}P$ quantum well structures with strain compensation 164 (1996) 276
Yazawa, Y., see Kondow 164 (1996) 175
Yoshida, S., see Okumura 164 (1996) 92
Yoshida, S., see Okumura 164 (1996) 149
Yoshida, S. and M. Sasaki, In situ selective area growth of GaAs, AlAs, and AlGaAs using MOMBE 164 (1996) 291
Yu, E.T., see Yan 164 (1996) 77

Zeng Yiping, see Wang Xiaoliang 164 (1996) 281
Zhang, J., A.K. Lees, A.G. Taylor, D. Raisbeck, N. Shukla, J.M. Fernández, B.A. Joyce and M.E. Pemble, In-situ monitoring of Si and SiGe growth on Si(001) surfaces during gas-source molecular beam epitaxy using reflectance anisotropy 164 (1996) 40
Zhang, J., see Naji 164 (1996) 58
Zhang, J., see Joyce 164 (1996) 214
Zhang, J., see Fernández 164 (1996) 241
Zhang, S., J. Cui and Y. Aoyagi, Growth control of GaAs using short-pulse supersonic beam epitaxy 164 (1996) 28
Zhang, X.M., see Fernández 164 (1996) 241
Zijlstra, T., see Werner 164 (1996) 223

ELSEVIER

Journal of Crystal Growth 164 (1996) 502–503

JOURNAL OF CRYSTAL GROWTH

Subject index

Aluminum
– antimonide 491
– arsenide 291, 454
– nitride 132, 143, 159
Apparatus
– for chemical beam epitaxy
– – of III–V compounds 1
– for laser assisted chemical beam epitaxy
– – of gallium arsenide 71
– for thin film growth
– – by molecular beam epitaxy, electron beam assisted
– – – of gallium arsenide 92

Device characterization
– diodes 334, 465, 491
– electronic materials 285, 383, 415, 485
– heterojunction 389
– lasers 308, 434, 485
– light emitting diodes 154
– optoelectronic materials 396
– quantum wells 241, 263, 276, 281, 434, 442, 485, 491
– quantum wires 356
– transistors 223, 362, 389, 454, 460, 476
– wave guides 449
Diamond 208
Diffusional control
– of zinc 402
Diodes, see Device characterization
Doping
– of III–V by carbon 362, 371, 377, 383, 389, 425
– of III–V by sulphur 415

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– chemical 97
– reactive ion 308

Gallium
– aluminum arsenide 1, 22, 28, 291, 371, 485
– aluminum nitride 154
– aluminum phosphide 248
– antimonide 117, 491
– arsenide 1, 51, 58, 66, 71, 77, 88, 112, 125, 185, 271, 291, 296, 356, 371, 383, 396, 485
– arsenide nitride 175
– arsenide phosphide 77, 92
– indium arsenide 51, 122, 263, 276, 281, 362, 371, 442, 454, 460, 485
– indium arsenide phosphide 16, 122, 314, 402, 449
– indium phosphide 1, 34, 47, 276, 302, 470
– nitride 143, 149, 154, 159, 167, 185
– nitride phosphide 180
– phosphide 34, 92, 112, 256, 271

Heterojunction, see Device characterization

Indium
– aluminum arsenide 460
– aluminum phosphide 47
– arsenide 66, 125, 334, 345
– arsenide phosphide 434
– gallium arsenide 327, 339, 356, 377, 389, 415, 470, 476
– gallium arsenide phosphide 321
– nitride 143
– phosphide 66, 84, 112, 263, 271, 281, 302, 308, 314, 321, 327, 339, 362, 389, 402, 409, 420, 425, 430, 442, 454, 460, 465, 470, 476

Kinetics
– of diffusion 302
– of growth 34, 58, 112, 167, 190, 202, 208, 214, 248, 302, 327
– of interface control 214, 409
– of nucleation 167, 190, 248, 302

Lasers, see Device characterization
Light emitting diodes, see Device characterization

Optoelectronic materials, see Device characterization

Phase diagram
– of indium arsenide 334
Precursor
– for doping 389
– for gallium antimonide 117
– for indium phosphide 104, 420

Quantum wells, see Device characterization
Quantum wires, see Device characterization

Silicon 40, 214, 223, 235, 241
– carbide 132
– germanium 40, 214, 223, 241
Superlattices, multilayers
– of III–V compounds 34, 263, 271, 302, 327, 442
Surface morphology
– of gallium arsenide 51, 71, 88, 125
– of indium antimonide 125
– of indium arsenide 125
– of indium gallium arsenide 51
– of indium phosphide 84, 409
– of silicon germanium 40
Surface structure
– of gallium nitride 149
– of gallium nitride phosphide 180
– of indium arsenide 125

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of gallium arsenide 28
– by chemical beam epitaxy
– – of aluminum antimonide 491
– – of aluminum arsenide 454
– – of aluminum nitride 143
– – of diamond 208
– – of gallium aluminum arsenide 1, 371, 485
– – of gallium antimonide 491
– – of gallium arsenide 1, 22, 51, 66, 71, 112, 125, 271, 356, 371, 383, 485
– – of gallium nitride 143
– – of gallium phosphide 112, 271
– – of indium arsenide 66, 125, 345
– – of indium gallium arsenide 51, 122, 263, 327, 356, 371, 377, 415, 442, 454, 470, 476, 485
– – of indium gallium arsenide phosphide 122
– – of indium gallium phosphide 1, 470
– – of indium nitride 143
– – of indium phosphide 66, 104, 112, 263, 271, 308, 327, 430, 442, 454, 465, 470, 476
– – of zinc selenide 190
– – of zinc sulphide 202
– by gas source molecular beam epitaxy
– – of aluminum nitride 132, 154, 159
– – of dysprosium phosphide 285
– – of gallium aluminum nitride 154
– – of gallium arsenide 77
– – of gallium arsenide phosphide 77
– – of gallium indium arsenide 281, 460
– – of gallium nitride 154, 159
– – of gallium phosphide 256
– – of indium aluminum arsenide 460
– – of indium aluminum phosphide 47
– – of indium gallium phosphide 47
– – of indium phosphide 84, 281, 460
– – of silicon 40, 214, 223, 241
– – of silicon carbide 132
– – of silicon germanium 40, 214, 223, 241
– – of zinc cadmium selenide 196
– – of zinc cadmium sulphide selenide 196
– – of zinc selenide 196
– by metalorganic molecular beam epitaxy
– – of aluminum gallium arsenide 291
– – of aluminum gallium phosphide 248
– – of gallium antimonide 117
– – of gallium arsenide 58, 291, 296, 396
– – of gallium indium arsenide phosphide 16, 314, 321, 362, 389, 402, 449
– – of gallium indium phosphide 34, 339
– – of gallium nitride phosphide 180
– – of gallium phosphide 34, 314, 321, 420
– – of indium arsenide 334
– – of indium arsenide phosphide 434
– – of indium phosphide 339, 362, 389, 402, 409, 425
– – of zinc cadmium selenide 196
– – of zinc cadmium sulphide selenide 196
– – of zinc selenide 196
– – theory of selective growth 302
– by molecular beam epitaxy
– – of gallium arsenide 88, 185
– – of gallium arsenide nitride 175
– – of gallium arsenide phosphide 92
– – of gallium indium arsenide 276
– – of gallium indium phosphide 276
– – of gallium nitride 149, 167, 175, 185
– – of gallium phosphide 92
– – of silicon 235
– – theory of facet formation 235
– by solid source molecular beam epitaxy
– – of dysprosium phosphide 285
– by vapor phase epitaxy
– – through metalorganic chemical vapor deposition
– – – of gallium arsenide 396
Transistors, see Device characterization

Wave guides, see Device characterization

Zinc
– cadmium selenide 196
– magnesium sulphide 196
– selenide selenide 190, 196
– sulphide 202